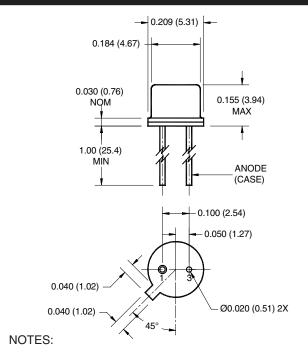


# **1N6265** GaAs INFRARED EMITTING DIODE

SEMICONDUCTOR®

## PACKAGE DIMENSIONS



- 1. Dimensions for all drawings are in inches (mm).
- 2. Tolerance of  $\pm$  .010 (.25) on all non-nominal dimensions unless otherwise specified.

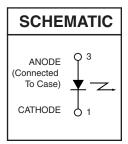
## FEATURES

- · Good optical to mechanical alignment
- Mechanically and wavelength matched to the TO-18 series phototransistor
- Hermetically sealed package
- High irradiance level
- (\*) Indicates JEDEC registered values

## DESCRIPTION

• The 1N6265 is a 940 nm LED in a narrow angle, TO-46 package.





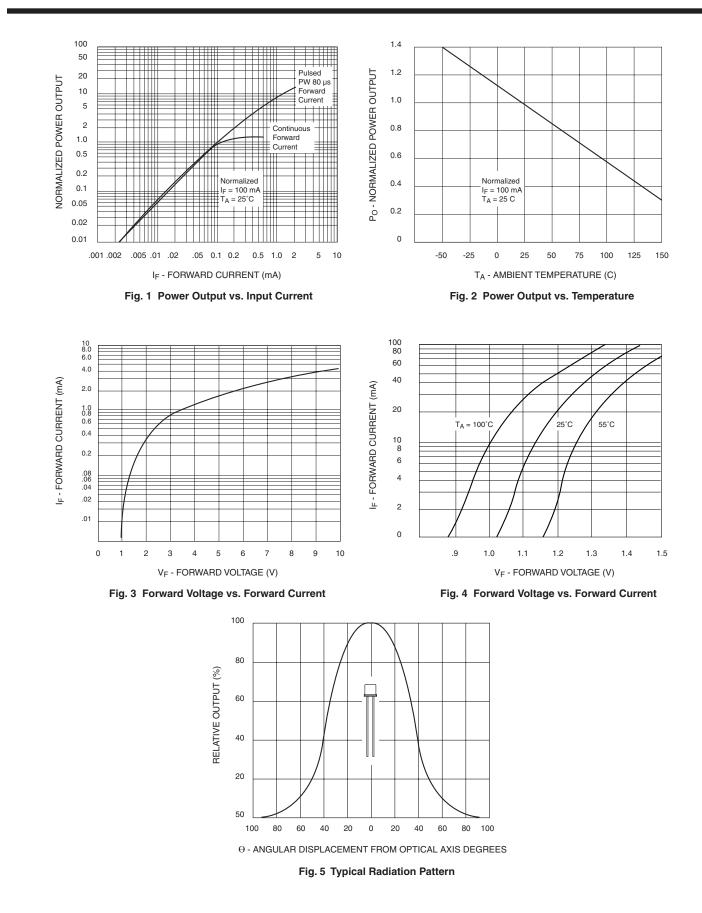
- 1. Derate power dissipation linearly 1.70 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 13.0 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension
- 7. Total power output,  $P_0$ , is the total power radiated by the device into a solid angle of 2  $\pi$  steradians.

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise specified) Symbol Unit Parameter Rating **Operating Temperature** -65 to +125 °C TOPR °C \*Storage Temperature -65 to +150 TSTG \*Soldering Temperature (Iron)(3,4,5 and 6) 240 for 5 sec °C T<sub>SOL-I</sub> \*Soldering Temperature (Flow)(3,4 and 6) 260 for 10 sec °C T<sub>SOL-F</sub> \*Continuous Forward Current 100 mΑ $I_{F}$ \*Forward Current (pw, 1µs; 200Hz) 10 $|_{F}$ А V \*Reverse Voltage $V_{R}$ 3 \*Power Dissipation $(T_A = 25^{\circ}C)^{(1)}$ 170 mW $P_D$ $P_D$ Power Dissipation $(T_C = 25^{\circ}C)^{(2)}$ 1.3 W

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNITS
*Peak Emission Wavelength	I <sub>F</sub> = 100 mA	$\lambda_{PE}$	935	—	955	nm
Emission Angle at 1/2 Power		θ		±40	—	Deg.
*Forward Voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>			1.7	V
*Reverse Leakage Current	V <sub>R</sub> = 3 V	I <sub>R</sub>			10	μA
*Total Power	I <sub>F</sub> = 100 mA	Po	6		—	mW
Rise Time 0-90% of output		t <sub>r</sub>		1.0	—	μs
Fall Time 100-10% of output		t <sub>f</sub>	—	1.0	—	μs

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- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.